

IN THE CLAIMS:

Claims 12, 27-29, 32-34, 40, 65, 68, 88 and 90 have been amended as follows:

12. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim [3] 1, wherein:

the film used in the resin sealing step is formed of an elastically deformable substance, and the ends of the protruding electrodes are caused to fall in the film when the resin layer is formed by using the mold; and

the film is detached from the resin layer in the protruding electrode exposing step so that the ends of the protruding electrodes can be exposed from the resin layer.

27. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim 1, wherein:

cutting position grooves are formed, before the resin sealing step is carried out, in the substrate so as to be located in positions in which the substrate is cut in the separating step; and

the substrate is cut in the cutting position grooves after being filled with the sealing resin.

28. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim 1, wherein:

a pair of stress relaxing grooves is formed, prior to the resin sealing step, so as to sandwich a position in which the substrate is to be cut; and

the substrate is cut in [the] a position interposed between the pair of stress relaxing grooves in the separating step.

29. (Amended) A method for fabricating semiconductor devices comprising:

a first separating step of cutting a substrate on which semiconductor elements having protruding electrodes are formed so that the semiconductor elements are separated from each other;

a resin sealing step of arranging the separated semiconductor elements on a base member and sealing a sealing resin so that a resin layer is formed;

a protruding electrode exposing step of exposing at least ends of the protruding electrodes from the resin layer; and

a second separating step, conducted after said protruding electrode exposing step, of cutting the resin layer together with the base member in positions between adjacent semiconductor elements, so that the semiconductor elements to which the resin layer is formed are separated from each other.

32. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim 1 [or 30], wherein positioning grooves are formed on a back surface of the resin layer of the substrate after the resin sealing step is executed and before the separating step is executed.

33. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim 32, wherein the positioning grooves [can be] are formed by subjecting the back surface to half scribing.

34. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim [3] 1, wherein:

the film used in the resin sealing step has projection or recess portions located in positions in which the film is not interfered with the projecting electrodes; and

recess or projection portions formed on the resin layer by the projection or recess portions are used for positioning after the resin sealing step is completed.

40. (Twice Amended) The method for mounting the semiconductor device as claimed in claim [18 or 36] 37 wherein the semiconductor device has an interposer having an outer connection means, and wherein an interval between the outer connection means is wider than an interval between the protruding electrodes.

65. (Amended) A method for fabricating a semiconductor device comprising:

an electrode plate forming step of forming a pattern on a metallic base so that an electrode plate is formed;

a chip mounting step of mounting semiconductor elements on the electrode plate and electrically connecting the semiconductor elements thereto;

a sealing resin forming step of forming a sealing resin which seals the semiconductor elements and the electrode plate; and

a cutting step of cutting the sealing resin and the electrode plate at boundaries between adjacent ones of the semiconductor elements so that the semiconductor devices are separated from each other,

wherein said sealing resin forming step is conducted by providing a film between said electrode plate and a mold.

68. (Twice Amended) The method for fabricating the semiconductor device as claimed in claim 65, wherein:

a chip attachment step of positioning the semiconductor elements on [the] a heat radiating member and attaching the semiconductor elements thereto before the chip mounting step is executed; and

the semiconductor elements attached to the heat radiating member are mounted to the electrode plate in the chip mounting step,

88. (Amended) A method for fabricating the semiconductor as claimed in claim 4, wherein the resin sealing step further comprises a film disposing step of providing a non-adhesive process film between contact surfaces of the upper mold and the first lower mold half body and the second lower mold half body.

90. (Amended) A method for fabricating a semiconductor device comprising:

a mold preparing step of preparing a mold including a first mold, and a second mold which is located so as to face the first mold, the second mold including a first half body having a shape corresponding to a shape of a substrate, and a second half body which is provided so as to surround the first half body and can be elevated with respect to the first half body, the first and second half bodies cooperating with each other so that a cavity to be filled with resin is defined;

a resin sealing step of placing the substrate on which a plurality of semiconductor elements equipped with protruding electrodes are formed in the mold and supplying resin to positions in which the protruding electrodes are provided so as to form a resin layer which seals the protruding electrodes and the substrate;

a protruding electrode exposing step of exposing at least end portions of the protruding electrodes from the resin layer; and

a separating step of cutting the substrate together with the resin layer so that the semiconductor elements are separated into each other,

wherein the resin sealing step disposes a film, between the protruding electrodes and the mold, which thus contacts the sealing resin through the film.